

Title (en)

BIPOLAR TRANSISTOR WITH AN IMPROVED BASE EMITTER JUNCTION AND METHOD FOR THE PRODUCTION THEREOF

Title (de)

BIPOLARTRANSISTOR MIT VERBESSERTEM BASIS-EMITTER- BERGANG UND VERFAHREN ZUR HERSTELLUNG

Title (fr)

TRANSISTOR BIPOLAIRE A JONCTION BASE-EMETTEUR AMELIOREE ET PROCEDE DE PRODUCTION

Publication

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Application

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Priority

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Abstract (en)

[origin: WO2004077571A1] The invention relates to an improved bipolar transistor comprising a substrate, a collector (K) embodied in the substrate, a monocrystalline base embodied in a base layer (BS) which is arranged above the collector and a monocrystalline emitter layer (ES) which is arranged above the base. According to the invention, the structure of the emitter layer is improved with the aid of an intermediate layer (ZS) which is arranged between the emitter layer and the base and which is embodied as an etching stop layer. Preferably, an epitaxially formed silicon carbide layer, which can be selectively etched against silicon, is used.

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IPC 8 full level

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Citation (search report)

See references of WO 2004077571A1

Citation (examination)

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- US 6043130 A 20000328 - GREGORY HAYDN JAMES [US]
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